ABSTRACT

A method is provided for determining the end point during cleaning etching of processing chambers by means of plasma etching, which is used for carrying out coating or etching processes during the manufacture of semiconductor components. The invention provides a method for effectively and reliably determining the end point during cleaning etching of processing chambers. The end point is determined by monitoring the DC bias voltage on the plasma generator which is used for the plasma cleaning etching in the processing chamber in an evaluation unit. The plasma cleaning etching process is terminated by stopping the supply of the process gases in the gas supply unit and by switching off the plasma generator upon reaching a predetermined DC bias voltage value which corresponds to completion of the cleaning etching process.